

**Investigation of strain relaxion mechanism in Si-SiO<sub>2</sub> system during the process of its formation**

Kropman, Daniel; Poll, V.; Kärner, T.; Ugaste, Ülo; **Mellikov, Enn**; Arbu, Uno; Paomets, V. Physica status solidi (a) 2003 / 2, p. 297-301 <https://onlinelibrary.wiley.com/doi/abs/10.1002/pssa.200306611>

**Point defects interaction with extended defects and impurities and its influence on the Si-SiO<sub>2</sub> system properties**

**Kropman, Daniel**; Arbu, Uno; Kärner, T.; Ugaste, Ülo; **Mellikov, Enn**; **Kauk, Marit**; Heinmaa, I.; **Samoson, Ago**; Medvid, A. Gettering and defect engineering in semiconductor technology. XI 2005 / p. 333-338 : ill